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Hyperfast Rectifier, 20 A FRED Pt[®] G5



LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS								
I _{F(AV)}	20 A							
V _R	600 V							
V _F at I _F at 125 °C	1.23 V							
t _{rr} (typ.)	22 ns							
T _J max.	175 °C							
Package	D ² PAK 2L (TO-263AB 2L)							
Circuit configuration	Single							

FEATURES

- Best in class forward voltage drop and switching losses trade off
- Optimized for high speed operation
- 175 °C maximum operating junction temperature
- Polyimide passivation
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- AEC-Q101 qualified meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

Featuring a unique combination of low conduction and switching losses, this rectifier is the right choice for soft switched and resonant converters, as well as medium frequency hard switching converters. This device is specifically designed to improve efficiency of high speed LLC output rectification stages of EV / HEV battery charging stations and high frequency stages of UPS applications.

MECHANICAL DATA

Case: D²PAK 2L (TO-263AB 2L)

Molding compound meets UL 94 V-0 flammability rating

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Repetitive peak reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 119 °C, D = 0.50	20							
Repetitive peak forward current	I _{FRM}	T _C = 119 °C, D = 0.50, f = 20 kHz	40	А						
Non-repetitive peak surge current	I _{FSM}	T_{C} = 25 °C, t_{p} = 10 ms, sine wave	200							
Operating junction and storage temperature	T _J , T _{Stg}		-55 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)										
PARAMETER	SYMBOL TEST CONDITIONS					UNITS				
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-					
	V	I _F = 20 A	-	1.37	1.68	V				
Forward voltage	V _F	I _F = 20 A, T _J = 125 °C	-	1.23	-					
Povereo lookago ourrent		$V_{R} = V_{R}$ rated	-	-	10					
Reverse leakage current	IR	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	-	500	μA				
Junction capacitance	CT	V _R = 200 V	-	25	-	pF				
Series inductance	L _S	Measured to lead 5 mm from package body	-	8	-	nH				

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 1
 Document Number: 96913

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HALOGEN

FREE



VS-E5TH2106S2LHM3

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)											
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS				
Reverse recovery time		$I_F = 1.0 \text{ A,d}I_F/\text{dt} =$	100 A/µs, V _R = 30 V	-	22	-					
	t _{rr}	T _J = 25 °C		-	39	-	ns				
		T _J = 125 °C		-	49	-					
Peak recovery current	1	T _J = 25 °C	I _F = 12 A dI _F /dt = 1000 A/µs	-	15	-	A				
	I _{RRM}	T _J = 125 °C	$V_{\rm R} = 400 \text{ V}$	-	23	-					
Reverse recovery charge	0	T _J = 25 °C		-	290	-	nC				
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	730	-					
Reverse recovery time	+	T _J = 25 °C		-	47	-	ns				
Reverse recovery time	t _{rr}	T _J = 125 °C		-	62	-					
Pool recovery ourrent		T _J = 25 °C	I _F = 20 A dI _F /dt = 1000 A/μs	-	15	-	A				
Peak recovery current	I _{RRM}	T _J = 125 °C	$V_{\rm B} = 400 \text{ V}$	-	23	-					
	0	T _J = 25 °C		-	400	-					
Reverse recovery charge	Q _{rr}	T _J = 125 °C		-	1000	-	nC				

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Thermal resistance, junction-to-case	R _{thJC}		-	-	1.72	°C/W				
Weight			-	2.0	-	g				
			-	0.07	-	oz.				
Maximum junction and storage temperature range	T _J , T _{Stg}		-55	-	175	°C				
Marking device		Case style D ² PAK 2L (TO-263AB 2L)	E5TH2106SH							

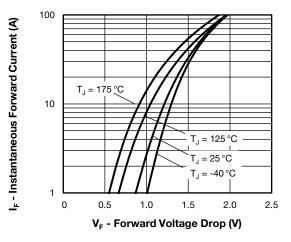


Fig. 1 - Forward Voltage Drop Characteristics

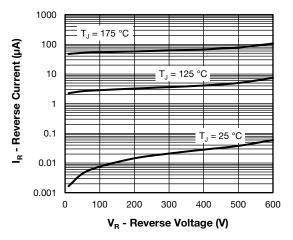


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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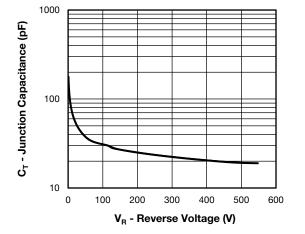
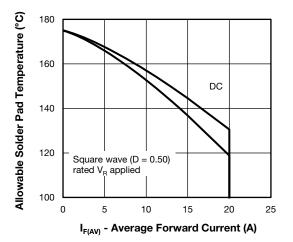
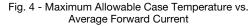


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage





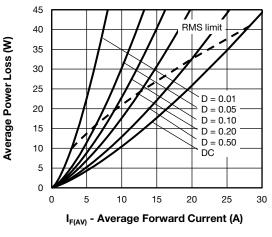


Fig. 5 - Forward Power Loss Characteristics

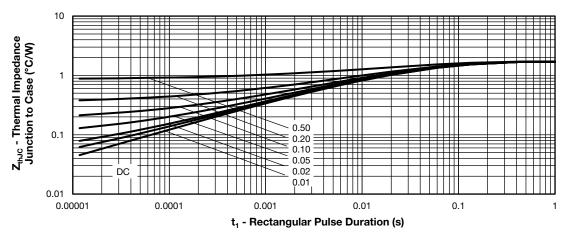


Fig. 6 - Transient Thermal Impedance, Junction to Case

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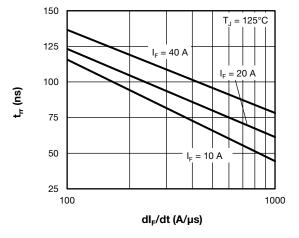


Fig. 7 - Typical Reverse Recovery Time vs. dI_F/dt

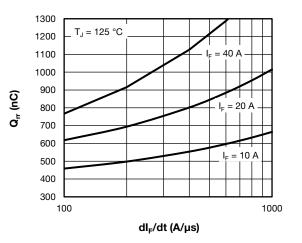


Fig. 8 - Typical Reverse Recovery Charge vs. dl_F/dt

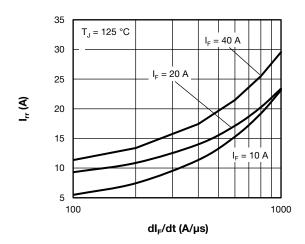


Fig. 9 - Typical Reverse Recovery Current vs. dl_F/dt

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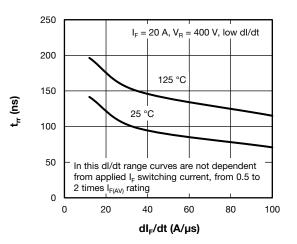


Fig. 10 - Typical Reverse Recovery Time vs. dl_F/dt

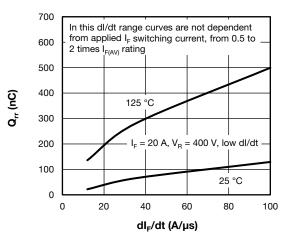


Fig. 11 - Typical Reverse Recovery Charge vs. dl_F/dt

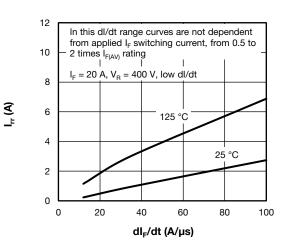


Fig. 12 - Typical Reverse Recovery Current vs. dl_F/dt

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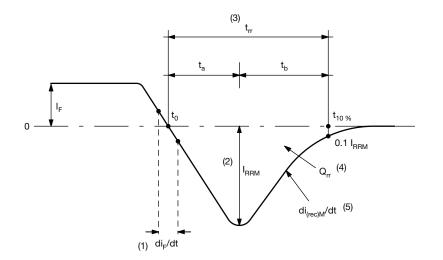


Fig. 13 - Reverse Recovery Waveform and Definitions

- Notes ⁽¹⁾ di_F/dt - rate of change of current through zero crossing
- $^{(2)}\ \ I_{RRM}$ peak reverse recovery current
- ⁽³⁾ t_{rr} reverse recovery time measured from t_0 , crossing point of negative going I_F, to point $t_{10\%}$, 0.1 I_{RRM} ⁽⁴⁾ Q_{rr} area under curve defined by t_0 and $t_{10\%}$

$$Q_{rr} = \int_{t_0}^{t_{10\%}} I(t) dt$$

 $^{(5)}$ di_(rec)M/dt - peak rate of change of current during t_b portion of t_{rr}

VS-E5TH2106S2LHM3

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ORDERING INFORMATION TABLE

Device code	VS-	Е	5	т	н	21	06	S2	L	н	МЗ
		2	3	4	5	6	7	8	9	(10)	
	1 - Vishay Semiconductors product										
	2 -	- E=	single	diode							
	3 - 5 = FRED generation 5										
	4 - Package:										
	_	T = D ² PAK (TO-263) package									
	5 -	• H=	hyper	fast rec	overy						
	6 -	- Cu	rrent ra	ting (21	= 20 A)					
	7 -	- Voltage rating (06 = 600 V)									
	8	- S2	= true 2	2 pin D ²	² PAK						
	9	- No	ne = tu	be (50 p	oieces)						
	• L = tape and reel (left oriented, for D ² PAK package)										
	If needed different orientation/packaging, please contact factory										
	10 - H = AEC-Q101 qualified										
	11 ·	- En	vironme	ental dig	git:						
		M3	= halog	gen-free	e, RoHS	S-comp	oliant, a	nd term	nination	lead (F	b)-free

ORDERING INFORMATION (Example)							
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION					
VS-E5TH2106S2LHM3	800	13" diameter reel					

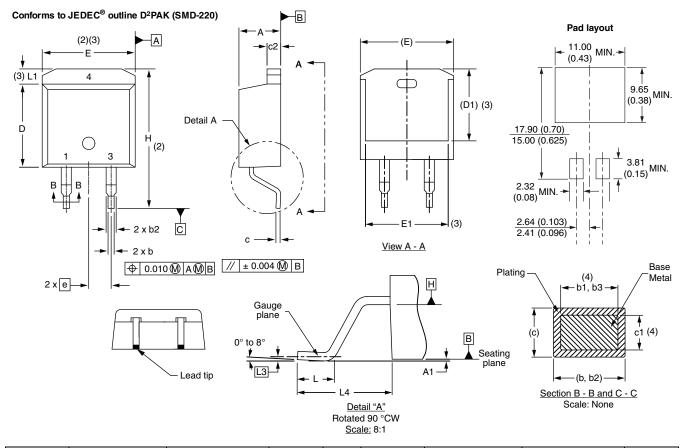
LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?96683
Part marking information	www.vishay.com/doc?96693
Packaging information	www.vishay.com/doc?95032





D²PAK 2L (TO-263AB 2L)

DIMENSIONS in millimeters and inches



SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIM	IETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	STWDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			Е	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L3	0.25 BSC		0.25 BSC 0.010 BSC		
c2	1.14	1.65	0.045	0.065			L4	4.78	5.28	0.188	0.208	
D	8.51	9.65	0.335	0.380	2							

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body
 (3) Thermal and contain antional within dimension E 1.1, D1 and E1.

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

(7) Outline conforms to JEDEC® outline TO-263AB

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